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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	e200z0h
Core Size	32-Bit Single-Core
Speed	64MHz
Connectivity	CANbus, LINbus, SPI, UART/USART
Peripherals	DMA, POR, PWM, WDT
Number of I/O	67
Program Memory Size	384KB (384K x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	36K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 3.6V
Data Converters	A/D 26x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/spc560p44l3ceabr

Table 3. SPC560P44Lx, SPC560P50Lx device configuration differences (continued)

Feature	Full-featured	Airbag
FlexRay	Yes	No
FMPLL (frequency-modulated phase-locked loop) module	2 (one FMPLL, one for FlexRay)	1 (only FMPLL)

1.4 Block diagram

Figure 1 shows a top-level block diagram of the SPC560P44Lx, SPC560P50Lx MCU.

Table 4. SPC560P44Lx, SPC560P50Lx series block summary

Block	Function
Analog-to-digital converter (ADC)	Multi-channel, 10-bit analog-to-digital converter
Boot assist module (BAM)	Block of read-only memory containing VLE code which is executed according to the boot mode of the device
Clock generation module (MC_CGM)	Provides logic and control required for the generation of system and peripheral clocks
Controller area network (FlexCAN)	Supports the standard CAN communications protocol
Cross triggering unit (CTU)	Enables synchronization of ADC conversions with a timer event from the eMIOS or from the PIT
Crossbar switch (XBAR)	Supports simultaneous connections between two master ports and three slave ports; supports a 32-bit address bus width and a 32-bit data bus width
Cyclic redundancy check (CRC)	CRC checksum generator
Deserial serial peripheral interface (DSPI)	Provides a synchronous serial interface for communication with external devices
Enhanced direct memory access (eDMA)	Performs complex data transfers with minimal intervention from a host processor via "*n*" programmable channels
Enhanced timer (eTimer)	Provides enhanced programmable up/down modulo counting
Error correction status module (ECSM)	Provides a myriad of miscellaneous control functions for the device including program-visible information about configuration and revision levels, a reset status register, wakeup control for exiting sleep modes, and optional features such as information on memory errors reported by error-correcting codes
External oscillator (XOSC)	Provides an output clock used as input reference for FMPLL_0 or as reference clock for specific modules depending on system needs
Fault collection unit (FCU)	Provides functional safety to the device
Flash memory	Provides non-volatile storage for program code, constants and variables
Frequency-modulated phase-locked loop (FMPLL)	Generates high-speed system clocks and supports programmable frequency modulation
Interrupt controller (INTC)	Provides priority-based preemptive scheduling of interrupt requests
JTAG controller	Provides the means to test chip functionality and connectivity while remaining transparent to system logic when not in test mode
LINFlex controller	Manages a high number of LIN (Local Interconnect Network protocol) messages efficiently with minimum load on CPU
Mode entry module (MC_ME)	Provides a mechanism for controlling the device operational mode and mode transition sequences in all functional states; also manages the power control unit, reset generation module and clock generation module, and holds the configuration, control and status registers accessible for applications
Periodic interrupt timer (PIT)	Produces periodic interrupts and triggers
Peripheral bridge (PBRIDGE)	Interface between the system bus and on-chip peripherals
Power control unit (MC_PCU)	Reduces the overall power consumption by disconnecting parts of the device from the power supply via a power switching device; device components are grouped into sections called "power domains" which are controlled by the PCU

1.5.22 FlexRay

The FlexRay module provides the following features:

- Full implementation of FlexRay Protocol Specification 2.1
- 32 configurable message buffers can be handled
- Dual channel or single channel mode of operation, each as fast as 10 Mbit/s data rate
- Message buffers configurable as Tx, Rx or RxFIFO
- Message buffer size configurable
- Message filtering for all message buffers based on FrameID, cycle count and message ID
- Programmable acceptance filters for RxFIFO message buffers

1.5.23 Serial communication interface module (LINFlex)

The LINFlex (local interconnect network flexible) on the SPC560P44Lx, SPC560P50Lx features the following:

- Supports LIN Master mode, LIN Slave mode and UART mode
- LIN state machine compliant to LIN1.3, 2.0, and 2.1 specifications
- Handles LIN frame transmission and reception without CPU intervention
- LIN features
  - Autonomous LIN frame handling
  - Message buffer to store Identifier and as much as 8 data bytes
  - Supports message length as long as 64 bytes
  - Detection and flagging of LIN errors (sync field, delimiter, ID parity, bit framing, checksum, and time-out)
  - Classic or extended checksum calculation
  - Configurable Break duration as long as 36-bit times
  - Programmable baud rate prescalers (13-bit mantissa, 4-bit fractional)
  - Diagnostic features: Loop back; Self Test; LIN bus stuck dominant detection
  - Interrupt-driven operation with 16 interrupt sources
- LIN slave mode features
  - Autonomous LIN header handling
  - Autonomous LIN response handling
- UART mode
  - Full-duplex operation
  - Standard non return-to-zero (NRZ) mark/space format
  - Data buffers with 4-byte receive, 4-byte transmit
  - Configurable word length (8-bit or 9-bit words)
  - Error detection and flagging
  - Parity, Noise and Framing errors
  - Interrupt-driven operation with four interrupt sources
  - Separate transmitter and receiver CPU interrupt sources
  - 16-bit programmable baud-rate modulus counter and 16-bit fractional
  - 2 receiver wake-up methods

Table 7. Pin muxing (continued)

Port pin	Pad configuration register (PCR)	Alternate function[1], [2]	Functions	Peripheral[3]	I/O direction [4]	Pad speed[5]		Pin No.	
						SRC = 0	SRC = 1	100-pin	144-pin
A[14]	PCR[14]	ALT0 ALT1 ALT2 ALT3 —	GPIO[14] TXD ETC[4] — EIRQ[13]	SIUL Safety Port_0 eTimer_1 — SIUL	I/O O I/O — I	Slow	Medium	99	143
A[15]	PCR[15]	ALT0 ALT1 ALT2 ALT3 — —	GPIO[15] — ETC[5] — RXD EIRQ[14]	SIUL — eTimer_1 — Safety Port_0 SIUL	I/O — I/O — I I	Slow	Medium	100	144
Port B (16-bit)									
B[0]	PCR[16]	ALT0 ALT1 ALT2 ALT3 —	GPIO[16] TXD ETC[2] DEBUG[0] EIRQ[15]	SIUL FlexCAN_0 eTimer_1 SSCM SIUL	I/O O I/O — I	Slow	Medium	76	109
B[1]	PCR[17]	ALT0 ALT1 ALT2 ALT3 — —	GPIO[17] — ETC[3] DEBUG[1] RXD EIRQ[16]	SIUL — eTimer_1 SSCM FlexCAN_0 SIUL	I/O — I/O — I I	Slow	Medium	77	110
B[2]	PCR[18]	ALT0 ALT1 ALT2 ALT3 —	GPIO[18] TXD — DEBUG[2] EIRQ[17]	SIUL LIN_0 — SSCM SIUL	I/O O — — I	Slow	Medium	79	114
B[3]	PCR[19]	ALT0 ALT1 ALT2 ALT3 —	GPIO[19] — — DEBUG[3] RXD	SIUL — — SSCM LIN_0	I/O — — — I	Slow	Medium	80	116
B[6]	PCR[22]	ALT0 ALT1 ALT2 ALT3 —	GPIO[22] CLKOUT CS2 — EIRQ[18]	SIUL MC_CGL DSPI_2 — SIUL	I/O O O — I	Slow	Medium	96	138

Table 7. Pin muxing (continued)

Port pin	Pad configuration register (PCR)	Alternate function[1],[2]	Functions	Peripheral[3]	I/O direction[4]	Pad speed[5]		Pin No.	
						SRC = 0	SRC = 1	100-pin	144-pin
B[7]	PCR[23]	ALT0 ALT1 ALT2 ALT3 — —	GPIO[23] — — — AN[0] RXD	SIUL — — — ADC_0 LIN_0	Input only	—	—	29	43
B[8]	PCR[24]	ALT0 ALT1 ALT2 ALT3 — —	GPIO[24] — — — AN[1] ETC[5]	SIUL — — — ADC_0 eTimer_0	Input only	—	—	31	47
B[9]	PCR[25]	ALT0 ALT1 ALT2 ALT3 —	GPIO[25] — — — AN[11]	SIUL — — — ADC_0 / ADC_1	Input only	—	—	35	52
B[10]	PCR[26]	ALT0 ALT1 ALT2 ALT3 —	GPIO[26] — — — AN[12]	SIUL — — — ADC_0 / ADC_1	Input only	—	—	36	53
B[11]	PCR[27]	ALT0 ALT1 ALT2 ALT3 —	GPIO[27] — — — AN[13]	SIUL — — — ADC_0 / ADC_1	Input only	—	—	37	54
B[12]	PCR[28]	ALT0 ALT1 ALT2 ALT3 —	GPIO[28] — — — AN[14]	SIUL — — — ADC_0 / ADC_1	Input only	—	—	38	55
B[13]	PCR[29]	ALT0 ALT1 ALT2 ALT3 — —	GPIO[29] — — — AN[0] RXD	SIUL — — — ADC_1 LIN_1	Input only	—	—	42	60

Table 7. Pin muxing (continued)

Port pin	Pad configuration register (PCR)	Alternate function[1], [2]	Functions	Peripheral[3]	I/O direction [4]	Pad speed[5]		Pin No.	
						SRC = 0	SRC = 1	100-pin	144-pin
D[14]	PCR[62]	ALT0 ALT1 ALT2 ALT3 —	GPIO[62] B[1] CS3 — SIN	SIUL FlexPWM_0 DSPI_3 — DSPI_3	I/O O O — I	Slow	Medium	73	105
D[15]	PCR[63]	ALT0 ALT1 ALT2 ALT3 —	GPIO[63] — — — AN[4]	SIUL — — — ADC_1	Input only	—	—	41	58
Port E(16-bit)									
E[0]	PCR[64]	ALT0 ALT1 ALT2 ALT3 —	GPIO[64] — — — AN[5]	SIUL — — — ADC_1	Input only	—	—	46	68
E[1]	PCR[65]	ALT0 ALT1 ALT2 ALT3 —	GPIO[65] — — — AN[4]	SIUL — — — ADC_0	Input only	—	—	27	39
E[2]	PCR[66]	ALT0 ALT1 ALT2 ALT3 —	GPIO[66] — — — AN[5]	SIUL — — — ADC_0	Input only	—	—	32	49
E[3]	PCR[67]	ALT0 ALT1 ALT2 ALT3 —	GPIO[67] — — — AN[6]	SIUL — — — ADC_0	Input only	—	—	—	40
E[4]	PCR[68]	ALT0 ALT1 ALT2 ALT3 —	GPIO[68] — — — AN[7]	SIUL — — — ADC_0	Input only	—	—	—	42

3 Electrical characteristics

3.1 Introduction

This section contains device electrical characteristics as well as temperature and power considerations.

This microcontroller contains input protection against damage due to high static voltages. However, it is advisable to take precautions to avoid application of any voltage higher than the specified maximum rated voltages.

To enhance reliability, unused inputs can be driven to an appropriate logic voltage level (V_{DD} or V_{SS}). This can be done by the internal pull-up or pull-down resistors, which are provided by the device for most general purpose pins.

The following tables provide the device characteristics and its demands on the system.

In the tables where the device logic provides signals with their respective timing characteristics, the symbol “CC” for Controller Characteristics is included in the Symbol column.

In the tables where the external system must provide signals with their respective timing characteristics to the device, the symbol “SR” for System Requirement is included in the Symbol column.

Caution: All of the following parameter values can vary depending on the application and must be confirmed during silicon characterization or silicon reliability trial.

3.2 Parameter classification

The electrical parameters are guaranteed by various methods. To give the customer a better understanding, the classifications listed in *Table 8* are used and the parameters are tagged accordingly in the tables where appropriate.

Table 8. Parameter classifications

Classification tag	Tag description
P	Those parameters are guaranteed during production testing on each individual device.
C	Those parameters are achieved by the design characterization by measuring a statistically relevant sample size across process variations.
T	Those parameters are achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values shown in the typical column are within this category.
D	Those parameters are derived mainly from simulations.

Note: The classification is shown in the column labeled “C” in the parameter tables where appropriate.

3.3 Absolute maximum ratings

Table 9. Absolute maximum ratings(1)

Symbol		Parameter	Conditions	Value		Unit
				Min	Max(2)	
V_{SS}	SR	Device ground	—	0	0	V
$V_{DD\_HV\_IOx}$(3)	SR	3.3 V / 5.0 V input/output supply voltage with respect to ground (V_{SS})	—	–0.3	6.0	V
$V_{SS\_HV\_IOx}$	SR	Input/output ground voltage with respect to ground (V_{SS})	—	–0.1	0.1	V
$V_{DD\_HV\_FL}$	SR	3.3 V / 5.0 V code and data flash supply voltage with respect to ground (V_{SS})	—	–0.3	6.0	V
			Relative to $V_{DD\_HV\_IOx}$		$V_{DD\_HV\_IOx}$ + 0.3	
$V_{SS\_HV\_FL}$	SR	Code and data flash ground with respect to ground (V_{SS})	—	–0.1	0.1	V
$V_{DD\_HV\_OSC}$	SR	3.3 V / 5.0 V crystal oscillator amplifier supply voltage with respect to ground (V_{SS})	—	–0.3	6.0	V
			Relative to $V_{DD\_HV\_IOx}$		$V_{DD\_HV\_IOx}$ + 0.3	
$V_{SS\_HV\_OSC}$	SR	3.3 V / 5.0 V crystal oscillator amplifier reference voltage with respect to ground (V_{SS})	—	–0.1	0.1	V
$V_{DD\_HV\_REG}$	SR	3.3 V / 5.0 V voltage regulator supply voltage with respect to ground (V_{SS})	—	–0.3	6.0	V
			Relative to $V_{DD\_HV\_IOx}$		$V_{DD\_HV\_IOx}$ + 0.3	
$V_{DD\_HV\_ADC0}$(4)	SR	3.3 V / 5.0 V ADC_0 supply and high reference voltage with respect to ground (V_{SS})	$V_{DD\_HV\_REG}$ < 2.7 V	–0.3	$V_{DD\_HV\_REG}$ + 0.3	V
			$V_{DD\_HV\_REG}$ > 2.7 V		6.0	
$V_{SS\_HV\_ADC0}$	SR	ADC_0 ground and low reference voltage with respect to ground (V_{SS})	—	–0.1	0.1	V
$V_{DD\_HV\_ADC1}$(4)	SR	3.3 V / 5.0 V ADC_0 supply and high reference voltage with respect to ground (V_{SS})	$V_{DD\_HV\_REG}$ < 2.7 V	–0.3	$V_{DD\_HV\_REG}$ + 0.3	V
			$V_{DD\_HV\_REG}$ > 2.7 V		6.0	
$V_{SS\_HV\_ADC1}$	SR	ADC_1 ground and low reference voltage with respect to ground (V_{SS})	—	–0.1	0.1	V
TV_{DD}	SR	Slope characteristics on all V_{DD} during power up(5) with respect to ground (V_{SS})	—	3.0	500 x 10^3 (0.5 [V/µs])	V/s
V_{IN}	SR	Voltage on any pin with respect to ground ($V_{SS\_HV\_IOx}$) with respect to ground (V_{SS})	—	–0.3	6.0	V
			Relative to $V_{DD\_HV\_IOx}$		$V_{DD\_HV\_IOx}$ + 0.3	

1. C.E. Triplett and B. Joiner, *An Experimental Characterization of a 272 PBGA Within an Automotive Engine Controller Module*, Proceedings of SemiTherm, San Diego, 1998, pp. 47–54.
2. G. Kromann, S. Shidore, and S. Addison, *Thermal Modeling of a PBGA for Air-Cooled Applications*, Electronic Packaging and Production, pp. 53–58, March 1998.
3. B. Joiner and V. Adams, *Measurement and Simulation of Junction to Board Thermal Resistance and Its Application in Thermal Modeling*, Proceedings of SemiTherm, San Diego, 1999, pp. 212–220.

3.6 Electromagnetic interference (EMI) characteristics

Table 14. EMI testing specifications

Symbol	Parameter	Conditions	Clocks	Frequency	Level (Max)	Unit
V_{EME}	Radiated emissions	Device configuration, test conditions and EM testing per standard IEC61967-2 Supply voltage = 5 V DC Ambient temperature = 25 °C Worst-case orientation	f_{OSC} 8 MHz f_{CPU} 64 MHz No PLL frequency modulation	150 kHz–150 MHz	16	dBµV
				150–1000 MHz	15	
				IEC Level	M	—
			f_{OSC} 8 MHz f_{CPU} 64 MHz 1% PLL frequency modulation	150 kHz–150 MHz	15	dBµV
				150–1000 MHz	14	
				IEC Level	M	—

3.7 Electrostatic discharge (ESD) characteristics

Table 15. ESD ratings(1),(2)

Symbol		Parameter	Conditions	Value	Unit
$V_{ESD(HBM)}$	S R	Electrostatic discharge (Human Body Model)	—	2000	V
$V_{ESD(CDM)}$	S R	Electrostatic discharge (Charged Device Model)	—	750 (corners)	V
				500 (other)	

1. All ESD testing is in conformity with CDF-AEC-Q100 Stress Test Qualification for Automotive Grade Integrated Circuits.
2. A device will be defined as a failure if after exposure to ESD pulses the device no longer meets the device specification requirements. Complete DC parametric and functional testing shall be performed per applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

3.8 Power management electrical characteristics

3.8.1 Voltage regulator electrical characteristics

The internal voltage regulator requires an external NPN ballast to be connected as shown in *Figure 9*. *Table 16* contains all approved NPN ballast components. Capacitances should be placed on the board as near as possible to the associated pins. Care should also be taken to limit the serial inductance of the $V_{DD\_HV\_REG}$, BCTRL and $V_{DD\_LV\_CORx}$ pins to less than

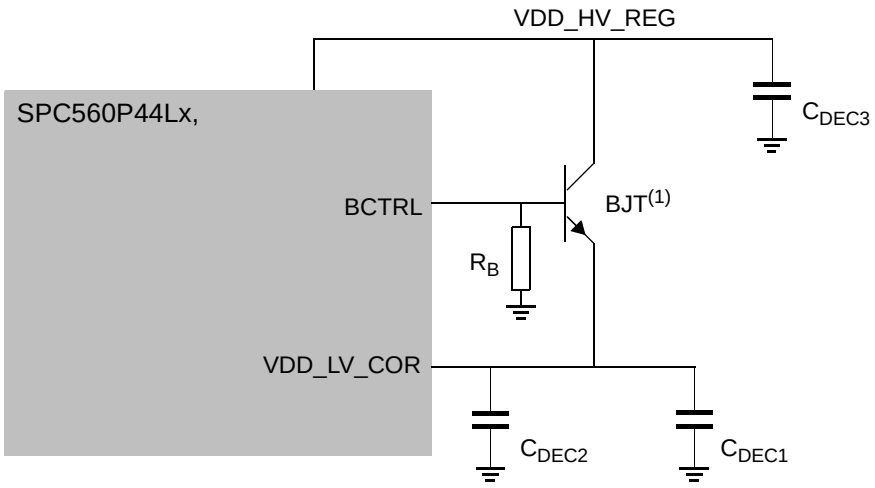
L_{Reg}, see *Table 17*.

Note: The voltage regulator output cannot be used to drive external circuits. Output pins are used only for decoupling capacitances.

$V_{DD\_LV\_COR}$ must be generated using internal regulator and external NPN transistor. It is not possible to provide $V_{DD\_LV\_COR}$ through external regulator.

For the SPC560P44Lx, SPC560P50Lx microcontroller, capacitors, with total values not below C_{DEC1}, should be placed between $V_{DD\_LV\_CORx}/V_{SS\_LV\_CORx}$ close to external ballast transistor emitter. 4 capacitors, with total values not below C_{DEC2}, should be placed close to microcontroller pins between each $V_{DD\_LV\_CORx}/V_{SS\_LV\_CORx}$ supply pairs and the $V_{DD\_LV\_REGCOR}/V_{SS\_LV\_REGCOR}$ pair . Additionally, capacitors with total values not below C_{DEC3}, should be placed between the $V_{DD\_HV\_REG}/V_{SS\_HV\_REG}$ pins close to ballast collector. Capacitors values have to take into account capacitor accuracy, aging and variation versus temperature.

All reported information are valid for voltage and temperature ranges described in recommended operating condition, *Table 10* and *Table 11*.



1. Refer to *Table 16*.

Figure 9. Configuration with resistor on base

Table 16. Approved NPN ballast components (configuration with resistor on base)

Part	Manufacturer	Approved derivatives(1)
BCP68	ON Semi	BCP68
	NXP	BCP68-25
	Infineon	BCP68-25
BCX68	Infineon	BCX68-10;BCX68-16;BCX68-25
BC868	NXP	BC868

Table 16. Approved NPN ballast components (configuration with resistor on base)

Part	Manufacturer	Approved derivatives(1)
BC817	Infineon	BC817-16;BC817-25;BC817SU;
	NXP	BC817-16;BC817-25
BCP56	ST	BCP56-16
	Infineon	BCP56-10;BCP56-16
	ON Semi	BCP56-10
	NXP	BCP56-10;BCP56-16

1. For automotive applications please check with the appropriate transistor vendor for automotive grade certification

Table 17. Voltage regulator electrical characteristics (configuration with resistor on base)

Symbol		C	Parameter	Conditions	Value			Unit
					Min	Typ	Max	
$V_{DD\_LV\_REGCOR}$	CC	P	Output voltage under maximum load run supply current configuration	Post-trimming	1.15	—	1.32	V
R_B	SR	—	External resistance on bipolar junction transistor (BJT) base	—	18	—	22	kΩ
C_{DEC1}	SR	—	External decoupling/stability ceramic capacitor	BJT from *Table 16*. 3 capacitances (i.e. X7R or X8R capacitors) with nominal value of 10 µF	19.5	30	—	µF
				BJT BC817, one capacitance of 22 µF	14.3	22		µF
R_{REG}	SR	—	Resulting ESR of all three capacitors of C_{DEC1}	BJT from *Table 16*. 3x10 µF. Absolute maximum value between 100 kHz and 10 MHz	—	—	50	mΩ
			Resulting ESR of the unique capacitor C_{DEC1}	BJT BC817, 1x 22 µF. Absolute maximum value between 100 kHz and 10 MHz	10	—	40	mΩ
C_{DEC2}	SR	—	External decoupling/stability ceramic capacitor	4 capacitances (i.e. X7R or X8R capacitors) with nominal value of 440 nF	1200	1760	—	nF
C_{DEC3}	SR	—	External decoupling/stability ceramic capacitor on $V_{DD\_HV\_REG}$	3 capacitances (i.e. X7R or X8R capacitors) with nominal value of 10 µF; C_{DEC3} has to be equal or greater than C_{DEC1}	19.5	30	—	µF
L_{Reg}	SR	—	Resulting ESL of $V_{DD\_HV\_REG}$, BCTRL and $V_{DD\_LV\_CORx}$ pins	—	—	—	15	nH

Table 23. DC electrical characteristics (3.3 V, NVUSRO[PAD3V5V] = 1)(1) (continued)

Symbol	C	Parameter	Conditions	Value		Unit
				Min	Max	
V_{IH}	P	High level input voltage	—	0.65 $V_{DD\_HV\_IOx}$	—	V
	D		—	—	$V_{DD\_HV\_IOx}$ + 0.1(2)	V
V_{HYS}	T	Schmitt trigger hysteresis	—	0.1 $V_{DD\_HV\_IOx}$	—	V
V_{OL_S}	P	Slow, low level output voltage	I_{OL} = 1.5 mA	—	0.5	V
V_{OH_S}	P	Slow, high level output voltage	I_{OH} = –1.5 mA	$V_{DD\_HV\_IOx}$ – 0.8	—	V
V_{OL_M}	P	Medium, low level output voltage	I_{OL} = 2 mA	—	0.5	V
V_{OH_M}	P	Medium, high level output voltage	I_{OH} = –2 mA	$V_{DD\_HV\_IOx}$ – 0.8	—	V
V_{OL_F}	P	Fast, low level output voltage	I_{OL} = 1.5 mA	—	0.5	V
V_{OH_F}	P	Fast, high level output voltage	I_{OH} = –1.5 mA	$V_{DD\_HV\_IOx}$ – 0.8	—	V
V_{OL_SYM}	P	Symmetric, low level output voltage	I_{OL} = 1.5 mA	—	0.5	V
V_{OH_SYM}	P	Symmetric, high level output voltage	I_{OH} = –1.5 mA	$V_{DD\_HV\_IOx}$ – 0.8	—	V
I_{PU}	P	Equivalent pull-up current	V_{IN} = V_{IL}	–130	—	µA
			V_{IN} = V_{IH}	—	–10	
I_{PD}	P	Equivalent pull-down current	V_{IN} = V_{IL}	10	—	µA
			V_{IN} = V_{IH}	—	130	
I_{IL}	P	Input leakage current (all bidirectional ports)	T_A = –40 to 125 °C	—	1	µA
I_{IL}	P	Input leakage current (all ADC input-only ports)	T_A = –40 to 125 °C	—	0.5	µA
C_{IN}	D	Input capacitance	—	—	10	pF
I_{PU}	D	$\overline{\text{RESET}}$, equivalent pull-up current	V_{IN} = V_{IL}	–130	—	µA
			V_{IN} = V_{IH}	—	–10	

1. These specifications are design targets and subject to change per device characterization.
2. “SR” parameter values must not exceed the absolute maximum ratings shown in *Table 9*.

Calling f_0 the bandwidth of the source signal (and as a consequence the cut-off frequency of the anti-aliasing filter, f_F), according to the Nyquist theorem the conversion rate f_C must be at least $2f_0$; it means that the constant time of the filter is greater than or at least equal to twice the conversion period (T_C). Again the conversion period T_C is longer than the sampling time T_S, which is just a portion of it, even when fixed channel continuous conversion mode is selected (fastest conversion rate at a specific channel): in conclusion it is evident that the time constant of the filter R_FC_F is definitively much higher than the sampling time T_S, so the charge level on C_S cannot be modified by the analog signal source during the time in which the sampling switch is closed.

The considerations above lead to impose new constraints on the external circuit, to reduce the accuracy error due to the voltage drop on C_S; from the two charge balance equations above, it is simple to derive *Equation 11* between the ideal and real sampled voltage on C_S:

Equation 11

$$\frac{V_A}{V_{A2}} = \frac{C_{P1} + C_{P2} + C_F}{C_{P1} + C_{P2} + C_F + C_S}$$

From this formula, in the worst case (when V_A is maximum, that is for instance 5 V), assuming to accept a maximum error of half a count, a constraint is evident on C_F value:

Equation 12

$$C_F > 2048 \bullet C_S$$

3.14.2 ADC conversion characteristics

Table 33. ADC conversion characteristics

Symbol		C	Parameter	Conditions(1)	Value			Unit
					Min	Typ	Max	
V_{INAN0}	SR		ADC0 and shared ADC0/1 analog input voltage(2), (3)	—	$V_{SS\_HV\_ADV0}$ – 0.3	—	$V_{DD\_HV\_ADV0}$ + 0.3	V
V_{INAN1}	SR		ADC1 analog input voltage(2), (4)	—	$V_{SS\_HV\_ADV1}$ – 0.3	—	$V_{DD\_HV\_ADV1}$ + 0.3	V
f_{CK}	SR	—	ADC clock frequency (depends on ADC configuration) (The duty cycle depends on AD_clk(5) frequency)	—	3(6)	—	60	MHz
f_s	SR	—	Sampling frequency	—	—	—	1.53	MHz
t_{ADC_S}	—	D	Sample time(7)	f_{ADC} = 20 MHz, INPSAMP = 3	125	—	—	ns
				f_{ADC} = 9 MHz, INPSAMP = 255	—	—	28.2	µs
t_{ADC_C}	—	P	Conversion time(8)	f_{ADC} = 20 MHz(9), INPCMP = 1	0.650	—	—	µs

Table 39. JTAG pin AC electrical characteristics (continued)

No.	Symbol		C	Parameter	Conditions	Value		Unit
						Min	Max	
5	t_{TMSH}, t_{TDIH}	CC	D	TMS, TDI data hold time	—	25	—	ns
6	t_{TDOV}	CC	D	TCK low to TDO data valid	—	—	40	ns
7	t_{TDOI}	CC	D	TCK low to TDO data invalid	—	0	—	ns
8	t_{TDOHZ}	CC	D	TCK low to TDO high impedance	—	40	—	ns
11	t_{BSDV}	CC	D	TCK falling edge to output valid	—	—	50	ns
12	t_{BSDVZ}	CC	D	TCK falling edge to output valid out of high impedance	—	—	50	ns
13	t_{BSDHZ}	CC	D	TCK falling edge to output high impedance	—	—	50	ns
14	t_{BSDST}	CC	D	Boundary scan input valid to TCK rising edge	—	50	—	ns
15	t_{BSDHT}	CC	D	TCK rising edge to boundary scan input invalid	—	50	—	ns

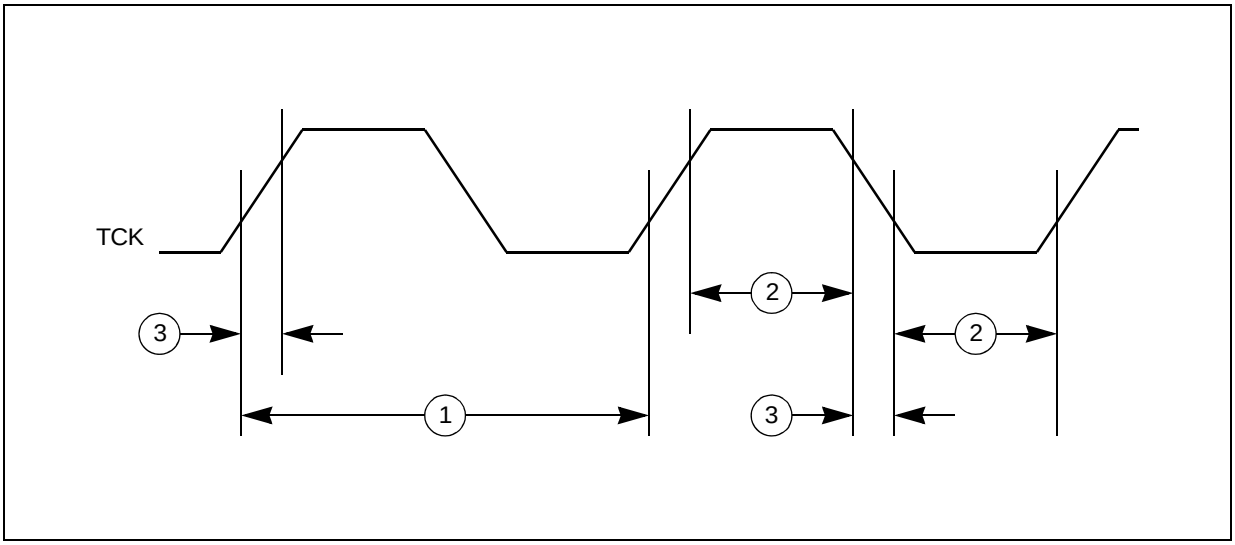


Figure 22. JTAG test clock input timing

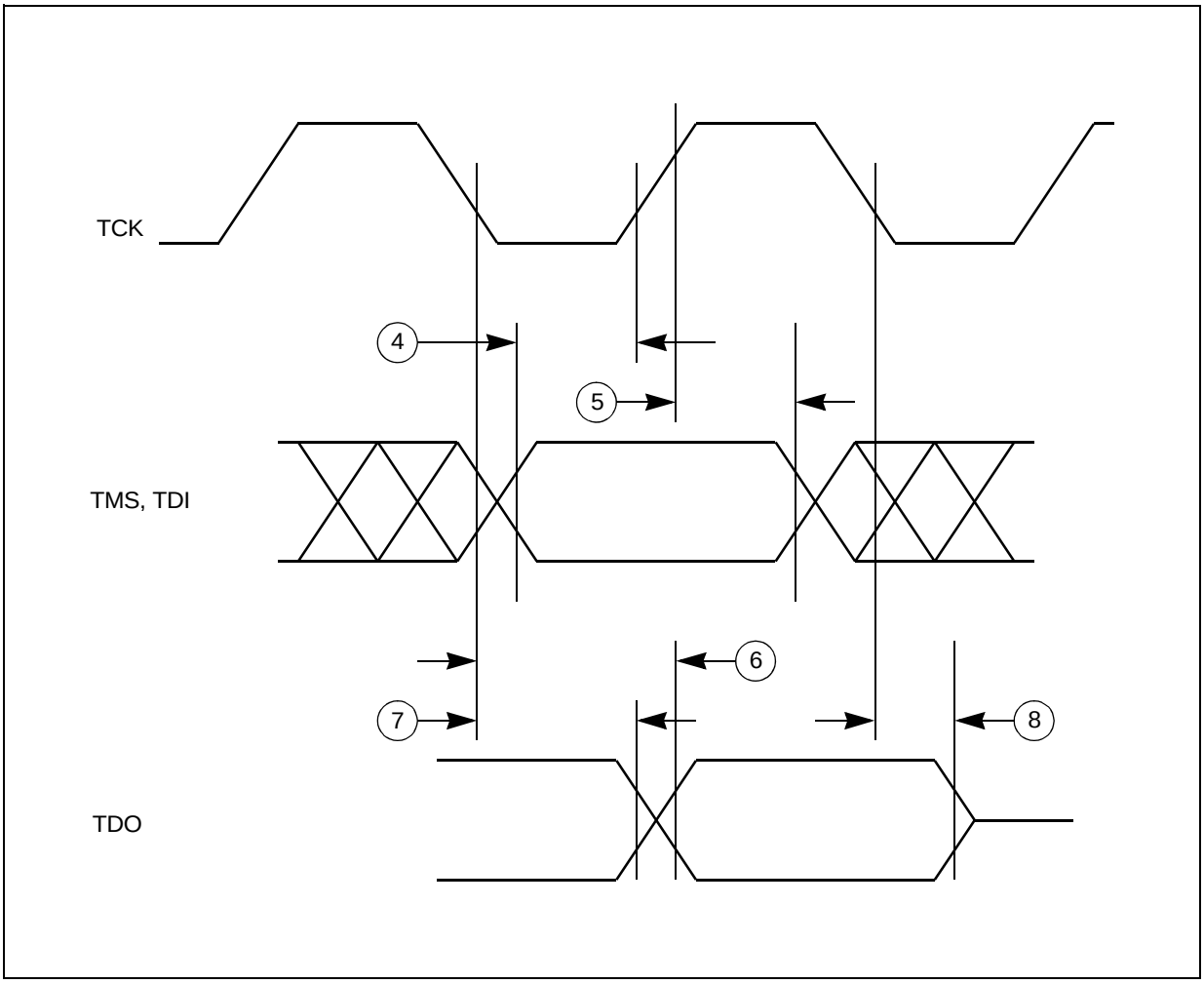


Figure 23. JTAG test access port timing

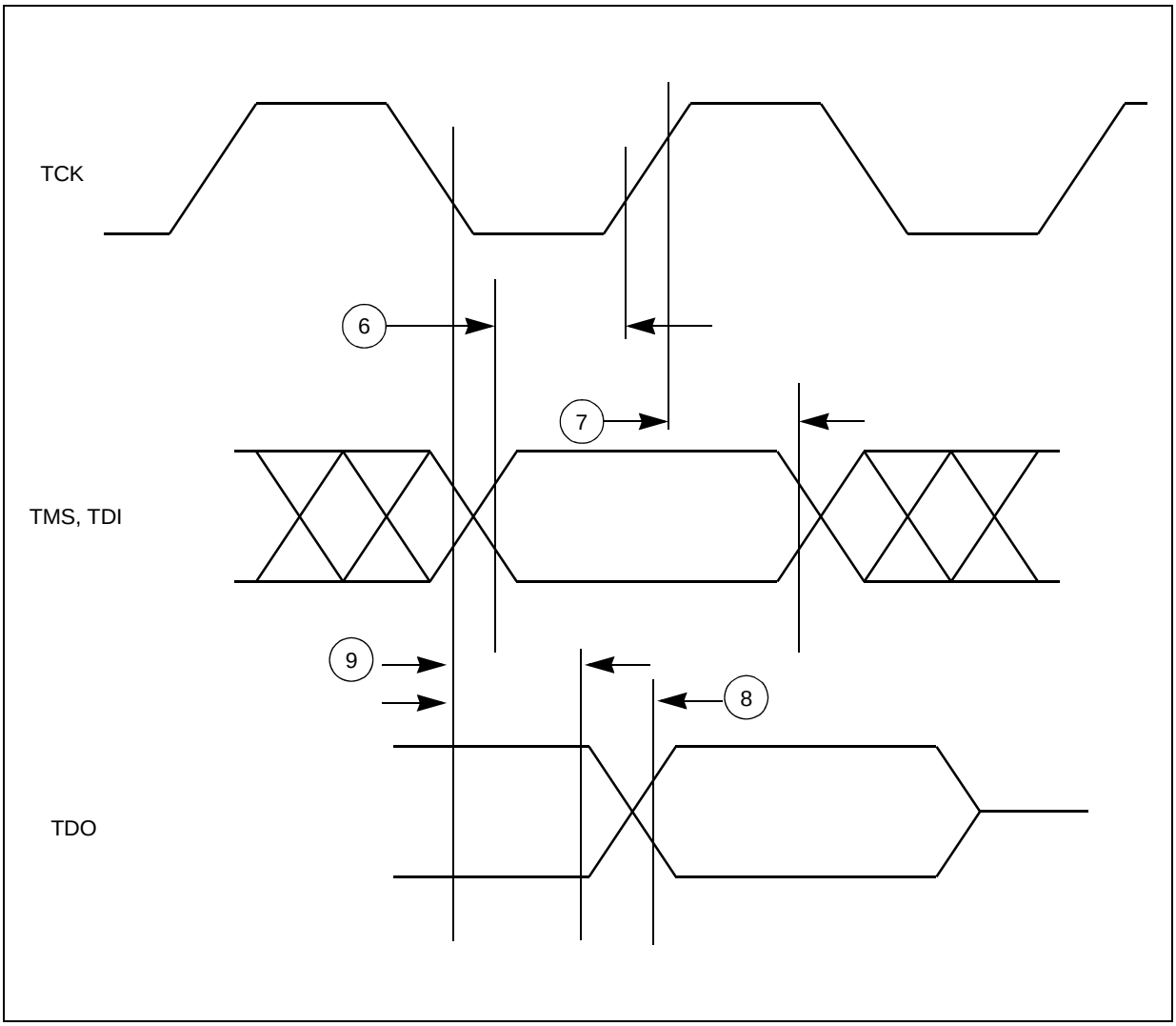


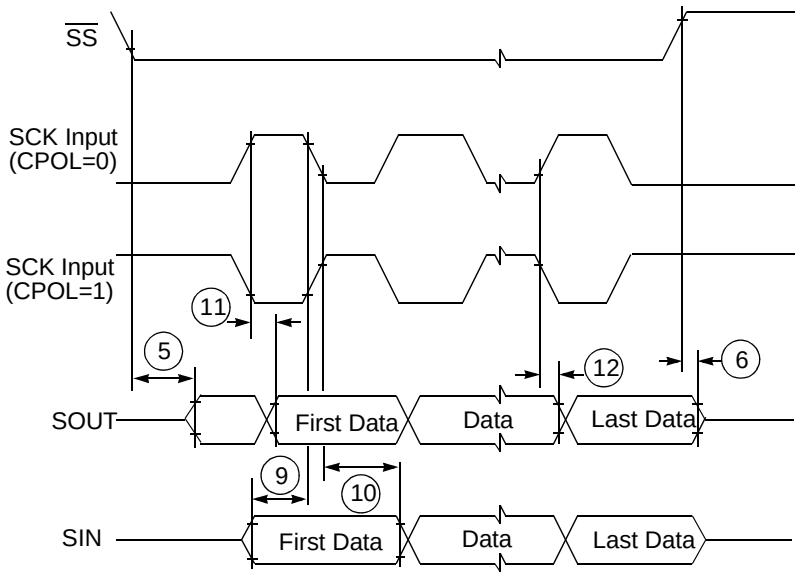
Figure 27. Nexus TDI, TMS, TDO timing

3.17.4 External interrupt timing (IRQ pin)

Table 41. External interrupt timing(1)

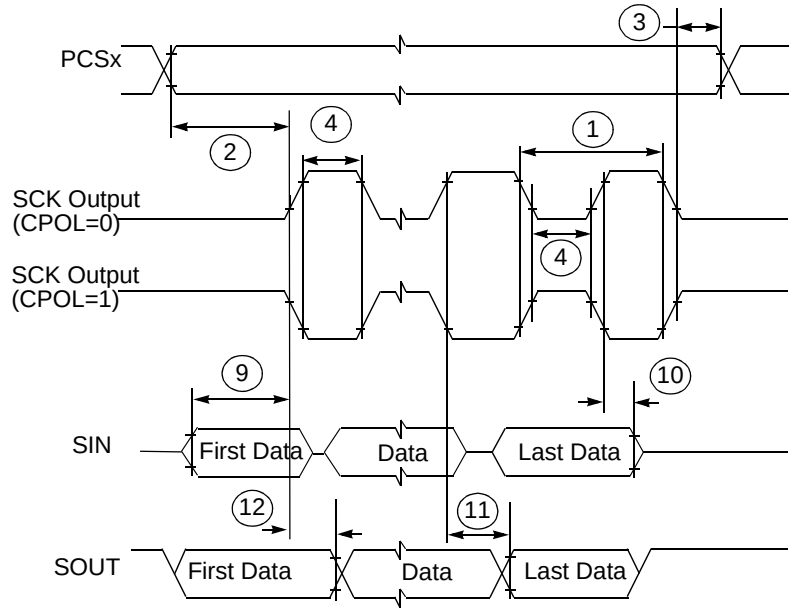
No.	Symbol		C	Parameter	Conditions	Value		Unit
						Min	Max	
1	t_{IPWL}	CC	D	IRQ pulse width low	—	4	—	t_{CYC}
2	t_{IPWH}	CC	D	IRQ pulse width high	—	4	—	t_{CYC}
3	t_{ICYC}	CC	D	IRQ edge to edge time(2)	—	4 + N (3)	—	t_{CYC}

1. IRQ timing specified at f_{SYS} = 64 MHz and $V_{DD\_HV\_IOx}$ = 3.0 V to 5.5 V, $T_A = T_L$ to T_H, and C_L = 200 pF with SRC = 0b00.
2. Applies when IRQ pins are configured for rising edge or falling edge events, but not both.
3. N = ISR time to clear the flag



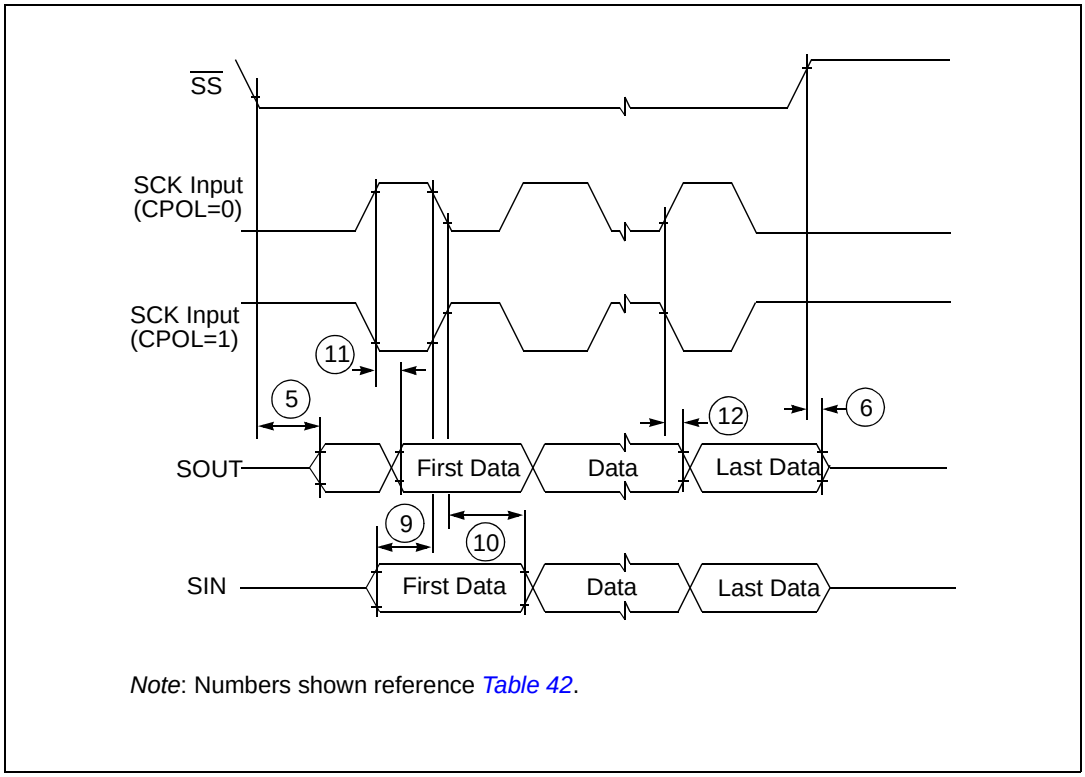
Note: Numbers shown reference *Table 42*.

Figure 32. DSPI classic SPI timing – Slave, CPHA = 1



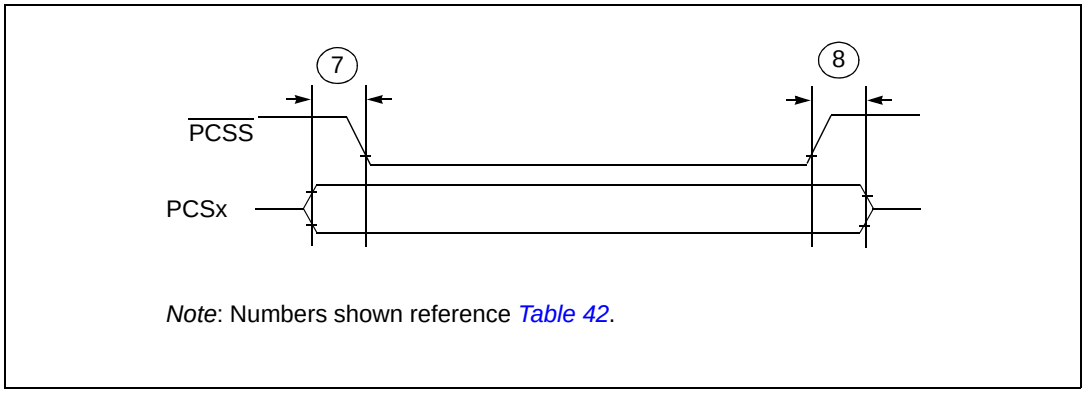
Note: Numbers shown reference *Table 42*.

Figure 33. DSPI modified transfer format timing – Master, CPHA = 0



Note: Numbers shown reference *Table 42*.

Figure 36. DSPI modified transfer format timing – Slave, CPHA = 1



Note: Numbers shown reference *Table 42*.

Figure 37. DSPI PCS strobe ($\overline{\text{PCSS}}$) timing

Table 46. Revision history (continued)

Date	Revision	Changes
18-Jul-2012	8	Updated *Table 1 (Device summary)* *Section 1.5.4, Flash memory*: Changed “Data flash memory: 32-bit ECC” to “Data flash memory: 64-bit ECC” *Figure 40 (Commercial product code structure)*, replaced "C = 60 MHz, 5 V" and "D = 60 MHz, 3.3 V" with respectively "C = 40 MHz, 5 V" and "D = 40 MHz, 3.3 V" *Table 9 (Absolute maximum ratings)*, updated TV_{DD} parameter, the minimum value to 3.0 V/s and the maximum value to 0.5 V/µs *Table 7 (Pin muxing)*, changed the description in the column "I/O direction" from "I/O" to "O" for the following port pins: A[10] with function B[0] A[11] with function A[0] A[11] with function A[2] A[12] with function A[2] A[12] with function B[2] A[13] with function B[2] C[7] with function A[1] C[10] with function A[3] C[15] with function A[1] D[0] with function B[1] D[10] with function A[0] D[11] with function B[0] D[13] with function A[1] D[14] with function B[1] Updated *Section 3.8.1, Voltage regulator electrical characteristics* Added *Table 27 (I/O consumption)* *Section 3.10, DC electrical characteristics*: deleted references to “oscillator margin” deleted subsection “NVUSRO[OSCILLATOR_MARGIN] field description” *Table 21 (DC electrical characteristics (5.0 V, NVUSRO[PAD3V5V] = 0))*, added IPU row for $\overline{\text{RESET}}$ pin *Table 23 (DC electrical characteristics (3.3 V, NVUSRO[PAD3V5V] = 1))*, added IPU row for $\overline{\text{RESET}}$ pin *Table 33 (ADC conversion characteristics)*, added V_{INAN} entry Removed “Order codes” table *Figure 40 (Commercial product code structure)*: added a footnote updated “E = Data flash memory”
18-Sep-2013	9	Updated Disclaimer